



81CXXX/81NXXX

CMOS IC

VOLTAGE DETECTORS WITH BUILT-IN DELAY TIME

DESCRIPTION

The UTC **81CXXX** and **81NXXX** series are good performance voltage detector and manufactured by CMOS technologies with highly accurate, low power consumption. A delay circuit is built-in to each detector, therefore, peripherals are unnecessary and high density mounting is possible. Detect voltage is extremely accurate with minimal temperature drift. Both CMOS and N-channel open drain output configurations are available.

FEATURES

- *Highly Accurate : Detect voltage $\pm 2\%$
- *Built-In Delay time : 1ms ~ 50ms,
50ms ~ 200ms,
200ms ~ 400ms,
- *Detect Voltage Temperature Characteristics:
TYP $\pm 100\text{ppm}/^\circ\text{C}$
- *Wide Operating Voltage Range : 0.7V ~ 10.0V
- *Low Current Consumption : TYP 1.0 μA ($V_{IN}=2.0\text{V}$)

ORDERING INFORMATION

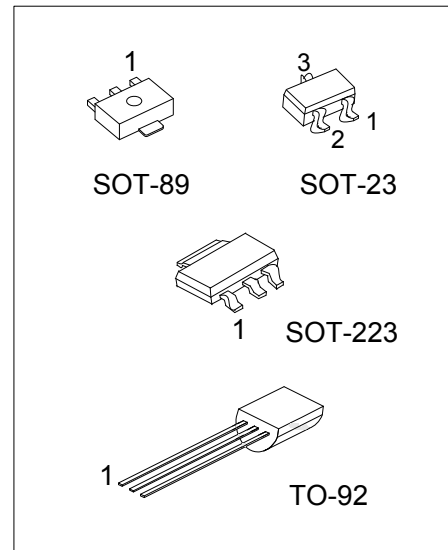
CMOS:

Ordering Number			①:Delay Time		Package	Pin Assign.			Packing
Normal	Lead Free Plating	Halogen Free	Duration	Code		1	2	3	
81Cxx-①-AA3-B-R	81CxxL-①-AA3-B-R	81CxxG-①-AA3-B-R	1 ~ 50 ms 50 ~ 200 ms 200 ~ 400 ms	P Q R	SOT-223	O	G	I	Tape Reel
81Cxx-①-AB3-E-R	81CxxL-①-AB3-E-R	81CxxG-①-AB3-E-R			SOT-89	O	I	G	Tape Reel
81Cxx-①-AE3-3-R	81CxxL-①-AE3-3-R	81CxxG-①-AE3-3-R			SOT-23	O	G	I	Tape Reel
81Cxx-①-AE3-5-R	81CxxL-①-AE3-5-R	81CxxG-①-AE3-5-R			SOT-23	G	O	I	Tape Reel
81Cxx-①-AE3-2-R	81CxxL-①-AE3-2-R	81CxxG-①-AE3-2-R			SOT-23	I	O	G	Tape Reel
81Cxx-①-T92-D-B	81CxxL-①-T92-D-B	81CxxG-①-T92-D-B			TO-92	I	G	O	Tape Box
81Cxx-①-T92-E-B	81CxxL-①-T92-E-B	81CxxG-①-T92-E-B			TO-92	O	I	G	Tape Box
81Cxx-①-T92-D-K	81CxxL-①-T92-D-K	81CxxG-①-T92-D-K			TO-92	I	G	O	Bulk
81Cxx-①-T92-E-K	81CxxL-①-T92-E-K	81CxxG-①-T92-E-K			TO-92	O	I	G	Bulk

N-Channel:

Ordering Number			①:Delay Time		Package	Pin Assign.			Packing
Normal	Lead Free Plating	Halogen Free	Duration	Code		1	2	3	
81Nxx-①-AA3-B-R	81NxxL-①-AA3-B-R	81NxxG-①-AA3-B-R	1 ~ 50 ms 50 ~ 200 ms 200 ~ 400 ms	H J K	SOT-223	O	G	I	Tape Reel
81Nxx-①-AB3-E-R	81NxxL-①-AB3-E-R	81NxxG-①-AB3-E-R			SOT-89	O	I	G	Tape Reel
81Nxx-①-AE3-3-R	81NxxL-①-AE3-3-R	81NxxG-①-AE3-3-R			SOT-23	O	G	I	Tape Reel
81Nxx-①-AE3-5-R	81NxxL-①-AE3-5-R	81NxxG-①-AE3-5-R			SOT-23	G	O	I	Tape Reel
81Nxx-①-AE3-2-R	81NxxL-①-AE3-2-R	81NxxG-①-AE3-2-R			SOT-23	I	O	G	Tape Reel
81Nxx-①-T92-D-B	81NxxL-①-T92-D-B	81NxxG-①-T92-D-B			TO-92	I	G	O	Tape Box
81Nxx-①-T92-E-B	81NxxL-①-T92-E-B	81NxxG-①-T92-E-B			TO-92	O	I	G	Tape Box
81Nxx-①-T92-D-K	81NxxL-①-T92-D-K	81NxxG-①-T92-D-K			TO-92	I	G	O	Bulk
81Nxx-①-T92-E-K	81NxxL-①-T92-E-K	81NxxG-①-T92-E-K			TO-92	O	I	G	Bulk

Note: 1. Pin assignment: I: V_{IN} O: V_{OUT} G: V_{SS}
2. xx: Output Voltage, refer to Marking Information.



Lead-free: 81CXXXL/81NXXXL
Halogen-free: 81CXXXG/81NXXXG

ORDERING INFORMATION(Cont.)

<p>81CxxL-①-AB3-x-R</p>	<p>(1) Packing Type (2) Pin Code (3) Package Type (4) Delay Time (5) Lead Plating (6) Output Voltage Code (7) Output Configuration</p>	<p>(1) R: Tape Reel, B: Tape Box, K: Bulk (2) refer to Pin Assignment (3) AA3: SOT-223, AB3: SOT-89, AE3: SOT-23, T92: TO-92 (4) ①: refer to Delay Time (5) G: Halogen Free, L: Lead Free, Blank: Pb/Sn (6) xx: refer to Marking Information (7) C: CMOS, N: N-Channel</p>
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MARKING INFORMATION

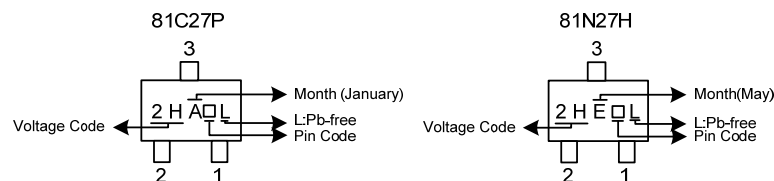
PACKAGE	VOLTAGE CODE	MARKING
SOT-223	10:1.0V	
	11:1.1V	
	12:1.2V	
SOT-89	13:1.3V	
	14:1.4V	
	15:1.5V	
	16:1.6V	
	17:1.7V	
	18:1.8V	
TO-92	19:1.9V	
	20:2.0V	
	21:2.1V	
	22:2.2V	
	23:2.3V	
	24:2.4V	
	25:2.5V	
	26:2.6V	
	27:2.7V	40:4.0V
	28:2.8V	41:4.1V
	29:2.9V	42:4.2V
	30:3.0V	43:4.3V
	31:3.1V	44:4.4V
	32:3.2V	45:4.5V
	33:3.3V	46:4.6V
	34:3.4V	47:4.7V
	35:3.5V	48:4.8V
	36:3.6V	49:4.9V
	37:3.7V	50:5.0V
	38:3.8V	
	39:3.9V	

PACKAGE	INTEGER*	CODE	DECIMAL**	CODE	MARKING
SOT-23	1.	1	.0	A	
	2.	2	.1	B	
	3.	3	.2	C	
	4.	4	.3	D	
	5.	5	.4	E	
	6.	6	.5	F	
			.6	G	
			.7	H	
			.8	J	
			.9	K	

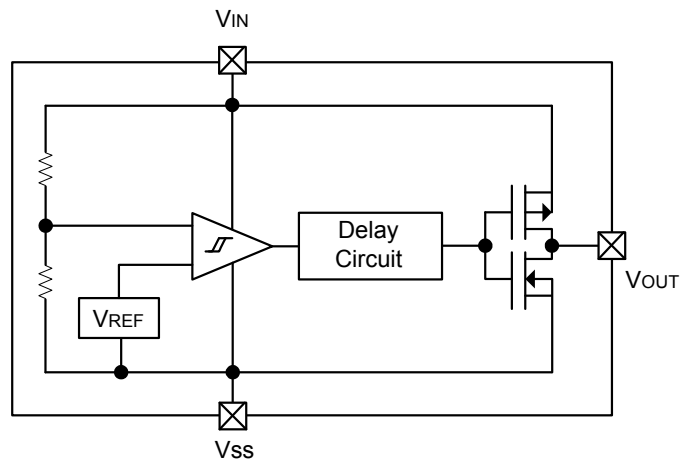
* Represents the integer of the Detect Voltage

** Represents the decimal number of the Detect Voltage

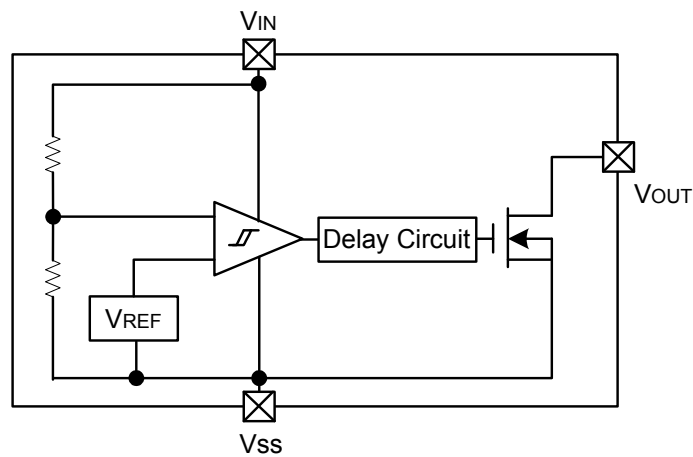
EXAMPLE:



■ BLOCK DIAGRAM



CMOS Output



N-channel Open Drain Output

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Input Voltage		V _{IN}	12	V
Output Current		I _{OUT}	50	mA
Output Voltage	CMOS	V _{OUT}	V _{SS} -0.3 ~ V _{IN} +0.3	V
	N-Ch open drain		V _{SS} -0.3 ~ 9	
Power Dissipation	SOT-223	P _D	800	mW
	SOT-23		150	
	SOT-89		500	
	TO-92		300	
Operating Temperature		T _{OPR}	-30 ~ +80	°C
Storage Temperature		T _{STG}	-40 ~ +125	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Thermal Resistance Junction-Case	SOT-223	θ _{JC}	15	°C/W
	SOT-23		200	
	SOT-89		100	
	TO-92		45	

■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Detection voltage (1.0V ~ 1.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V _{DF}	1		V _{DF} (T) X0.98	V _{DF} (T)	V _{DF} (T) X1.02	V
Hysteresis Range	V _{HYS}	1		V _{DF} X0.02	V _{DF} X0.05	V _{DF} X0.08	V
Operating Voltage	V _{IN}	1	V _{DF} =1.6V ~ 6.0V	0.7		10.0	V
Supply Current	I _{SS}	2	V _{IN} =1.5V		0.9	2.6	μA
			V _{IN} =5.0		2.0	4.2	μA
Output Current	I _{OUT}	3	N-ch V _{DS} =0.5V, V _{IN} =1.0V		2.2		mA
		4	P-ch V _{DS} =2.1V, V _{IN} =8.0V (CMOS output)		-15.4		mA
V _{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				±100		ppm/°C
Transient Delay Time (V _{DR} → V _{OUT} inversion)	t _{DLY} *	5	V _{IN} changes from 0.6V ~ 10V	50		200	ms

■ ELECTRICAL CHARACTERISTICS(Cont.)

Detection voltage (2.0V ~ 2.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF}(T)$ X0.98	$V_{DF}(T)$	$V_{DF}(T)$ X1.02	V
Hysteresis Range	V_{HYS}	1		V_{DF} X0.02	V_{DF} X0.05	V_{DF} X0.08	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=2.0V$		1.0	3.0	μA
			$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=2.0V$		7.9		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

Detection voltage (3.0V ~ 3.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF}(T)$ X0.98	$V_{DF}(T)$	$V_{DF}(T)$ X1.02	V
Hysteresis Range	V_{HYS}	1		V_{DF} X0.02	V_{DF} X0.05	V_{DF} X0.08	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=3.0V$		1.3	3.4	μA
			$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=3.0V$		10.1		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

■ ELECTRICAL CHARACTERISTICS(Cont.)

Detection voltage (4.0V ~ 4.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF(T)}$ X0.98	$V_{DF(T)}$	$V_{DF(T)}$ X1.02	V
Hysteresis Range	V_{HYS}	1		V_{DF} X0.02	V_{DF} X0.05	V_{DF} X0.08	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=4.0V$		1.5	3.8	μA
			$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=4.0V$		11.5		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

Detection voltage (5.0V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF(T)}$ X0.98	$V_{DF(T)}$	$V_{DF(T)}$ X1.02	V
Hysteresis Range	V_{HYS}	1		V_{DF} X0.02	V_{DF} X0.05	V_{DF} X0.08	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=5.0V$		13.0		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

$V_{DF(T)}$: established detect voltage value

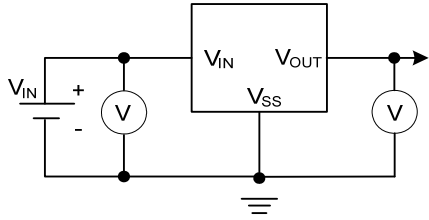
Release Voltage: $V_{DR} = V_{DF} + V_{HYS}$

* Transient Delay Time: 1ms ~ 50ms & 200ms ~ 400ms versions are also available.

Note: The power consumption during power-start to output being stable (release operation) is 2 μA greater than it is after that period (completion of release operation) because of delay circuit through current.

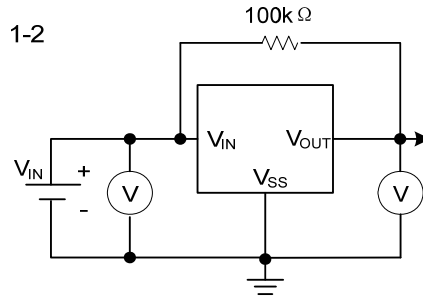
■ TEST CIRCUITS

1-1



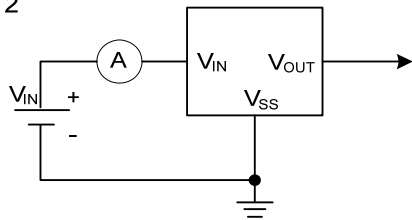
Cmos Output

1-2

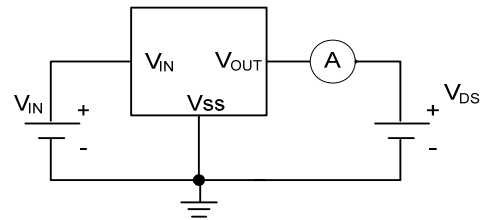


N-channel Open Drain Output

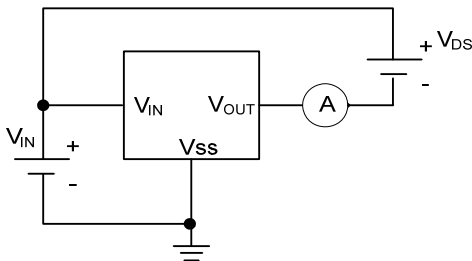
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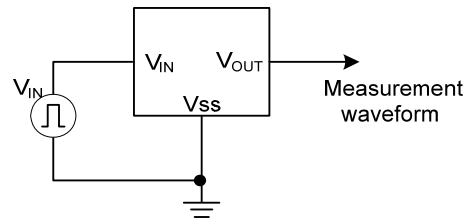
3



4

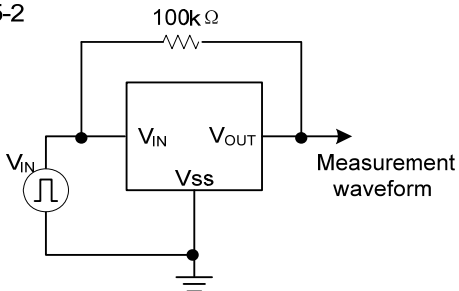


5-1



Cmos Output

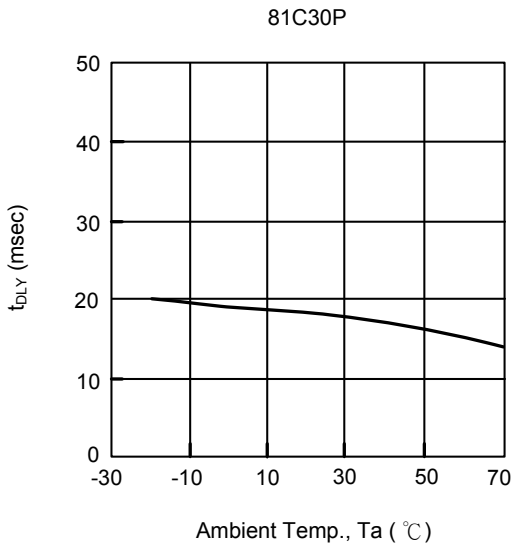
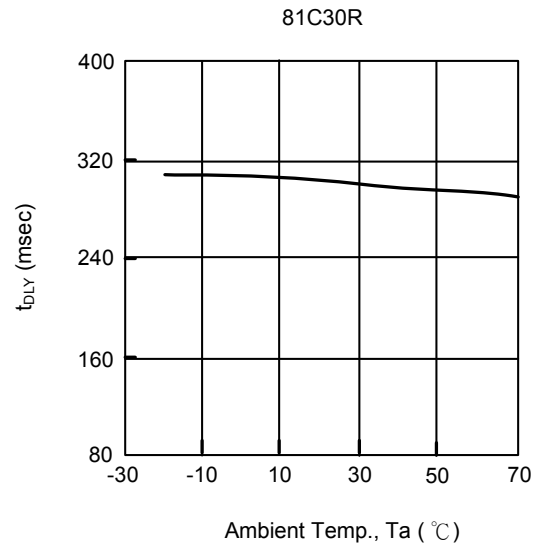
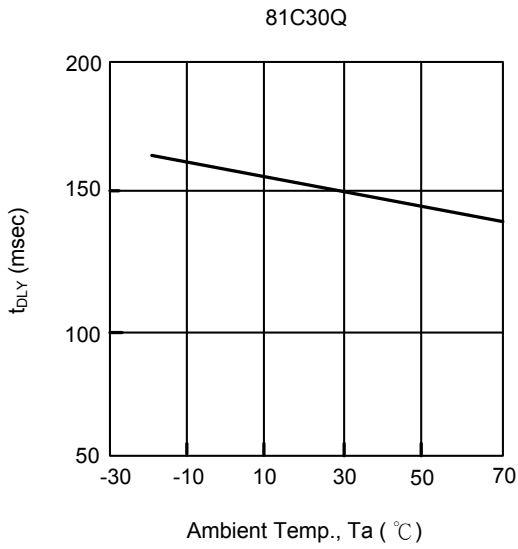
5-2



N-channel Open Drain Output

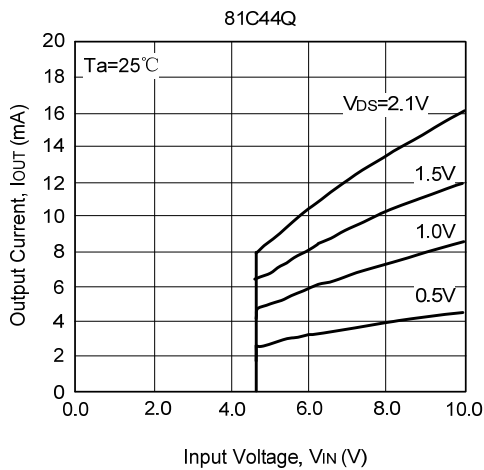
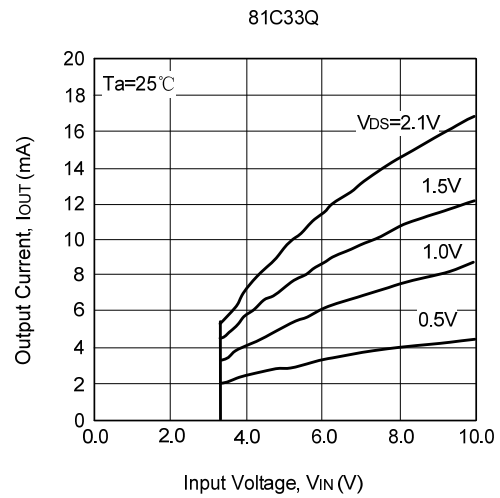
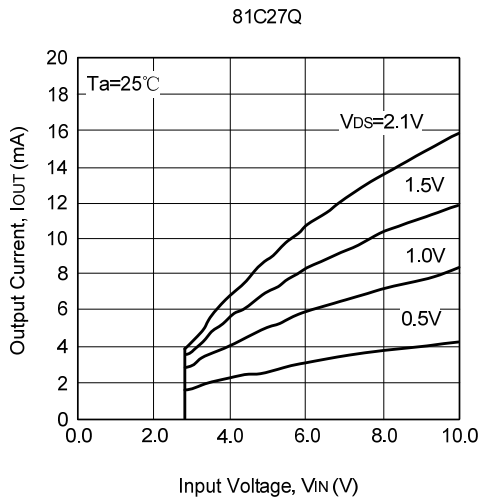
■ TYPICAL PERFORMANCE CHARACTERISTICS

(1) AMBIENT TEMPERATURE vs. TRANSIENT DELAY TIME

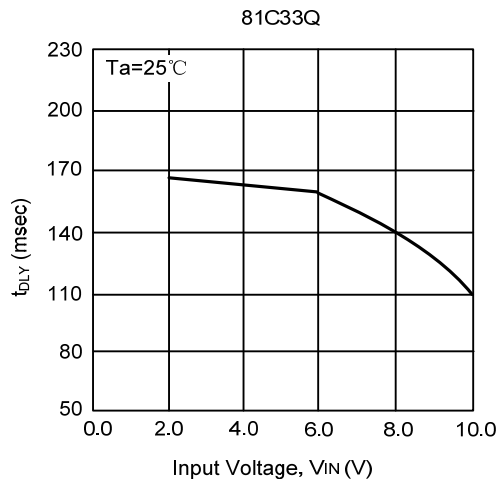


■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)

(2) P-CHANNEL DRIVER OUTPUT CURRENT vs. INPUT VOLTAGE

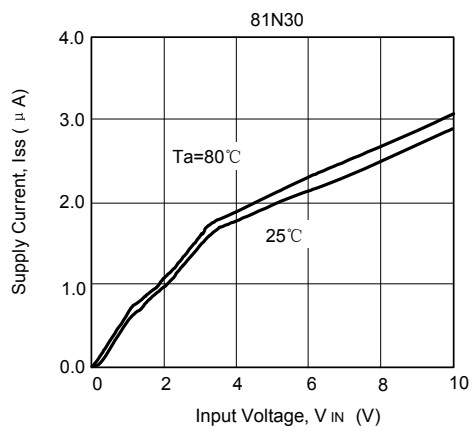
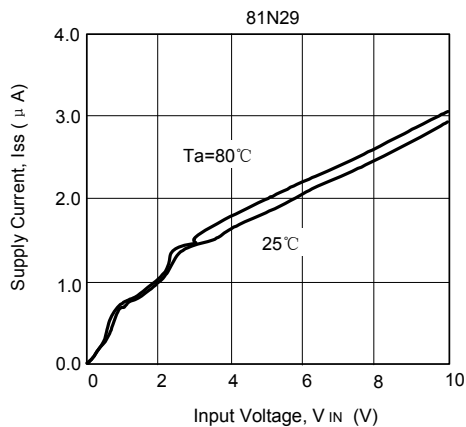
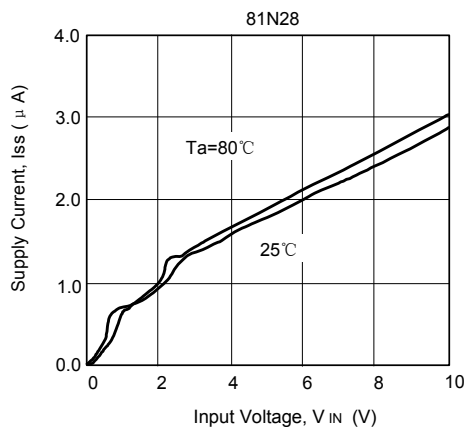
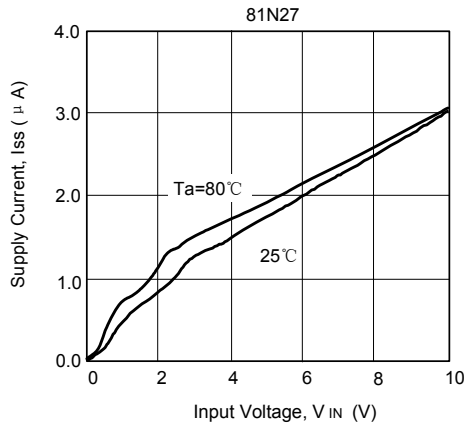
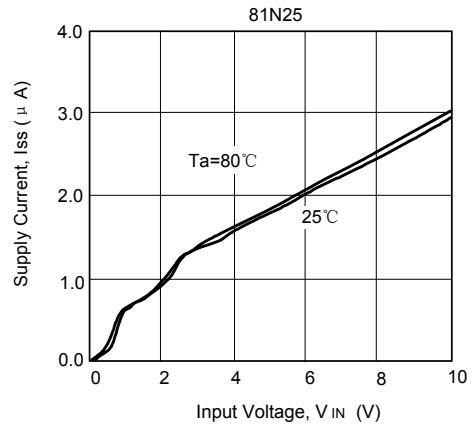
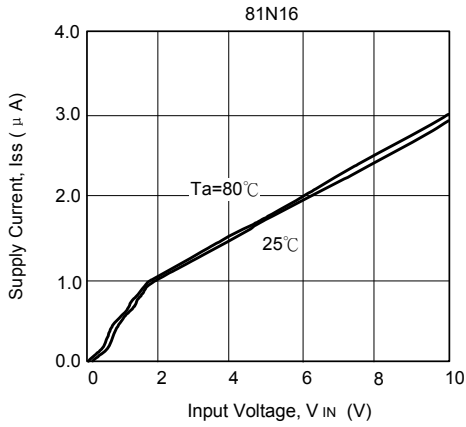


(2) TRANSIENT DELAY TIME vs. INPUT VOLTAGE

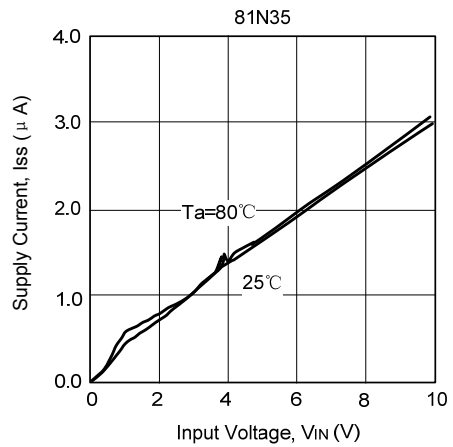
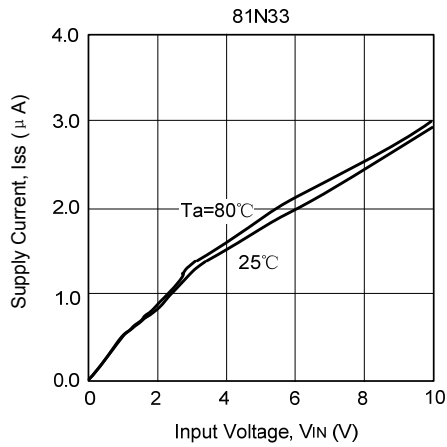


■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)

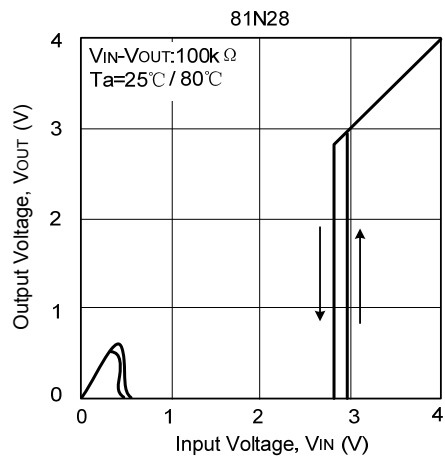
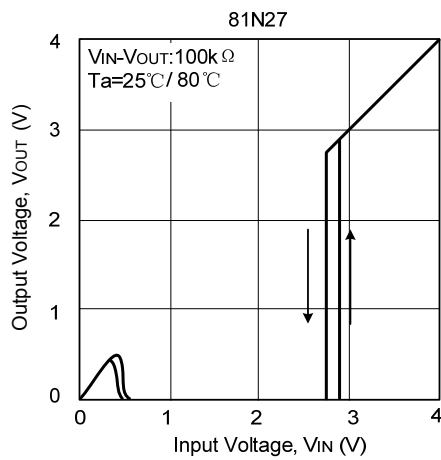
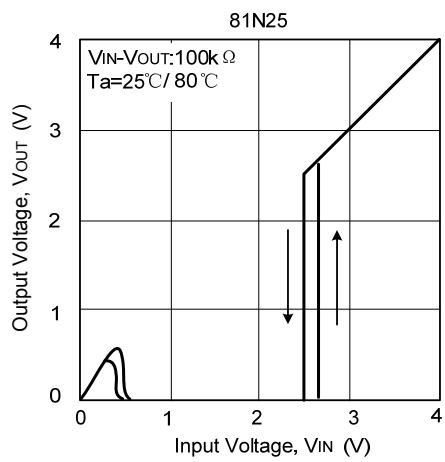
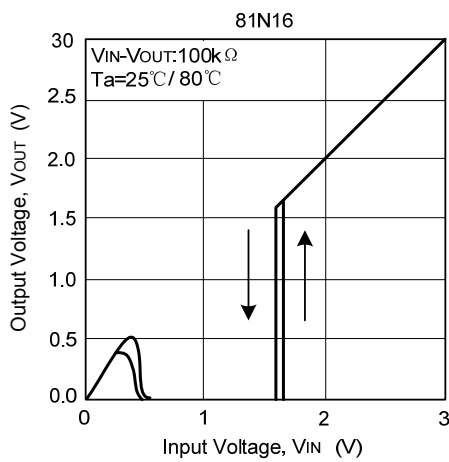
(3) SUPPLY CURRENT vs. INPUT VOLTAGE



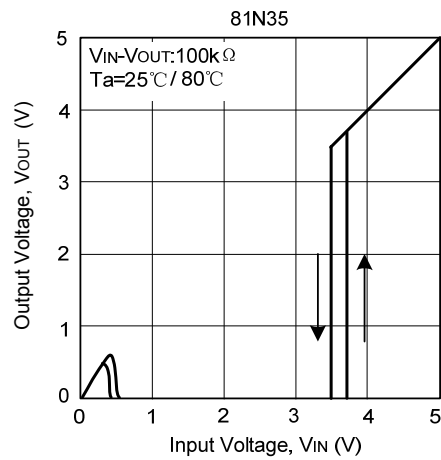
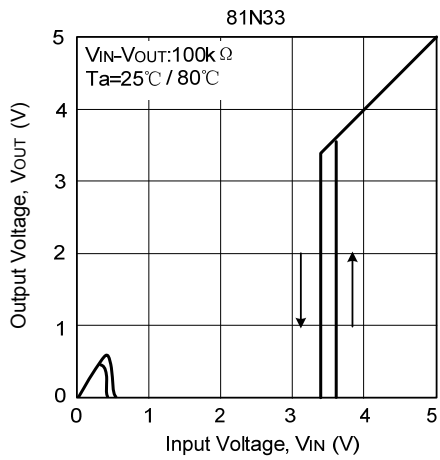
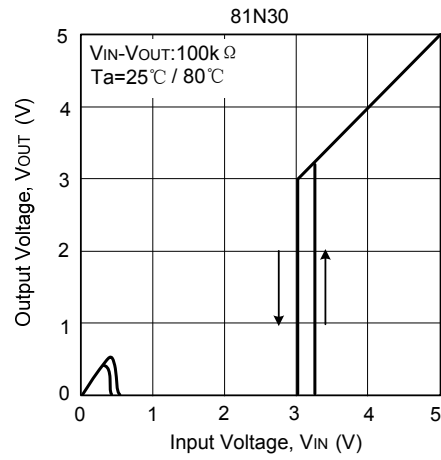
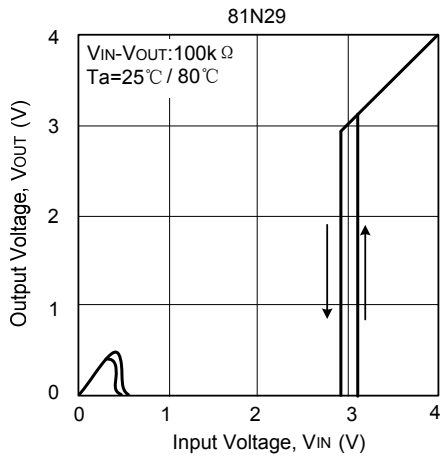
■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



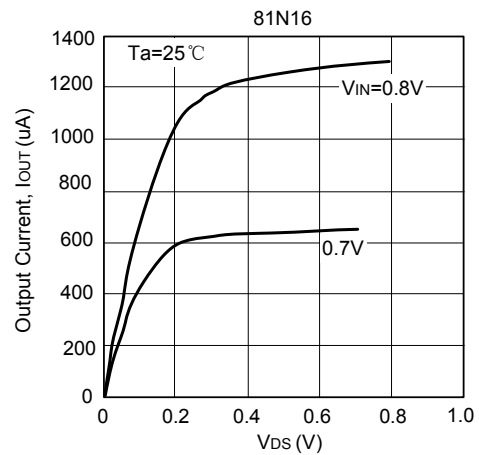
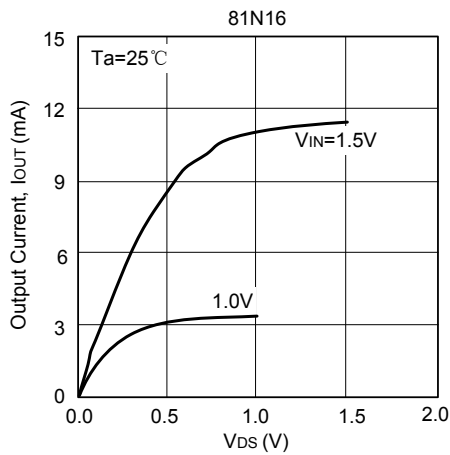
(4) OUTPUT VOLTAGE vs. INPUT VOLTAGE



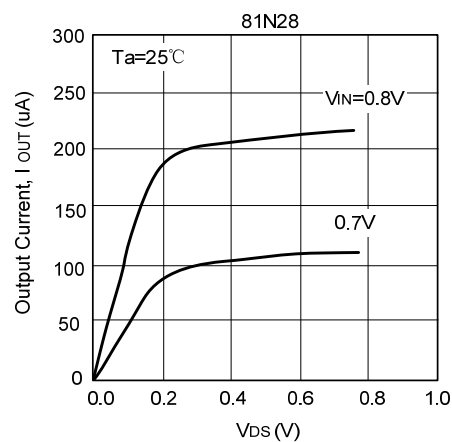
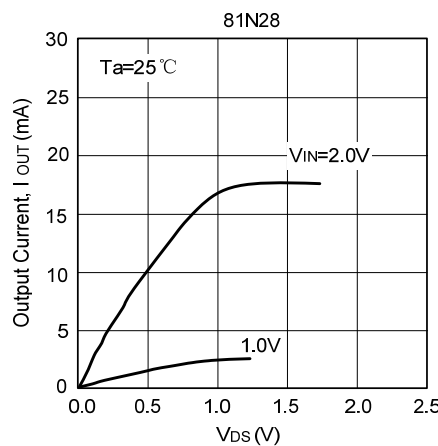
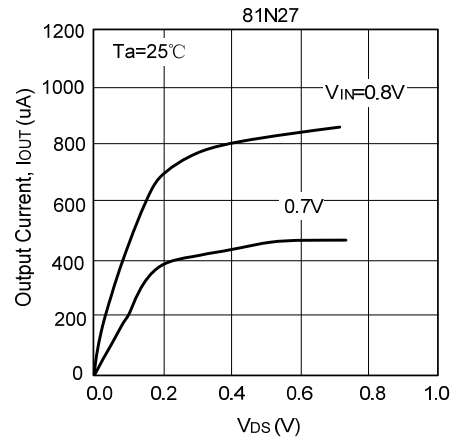
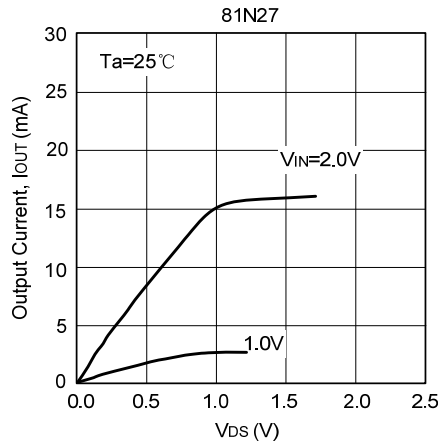
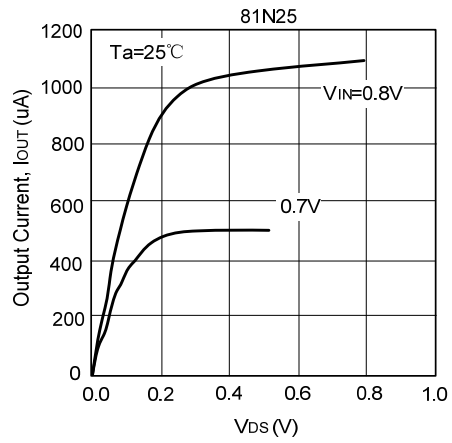
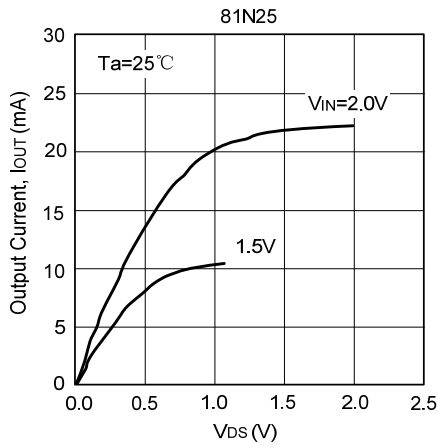
■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



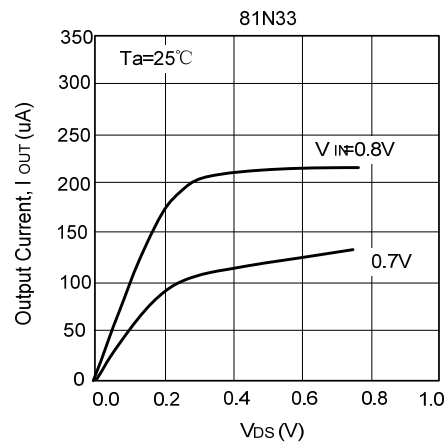
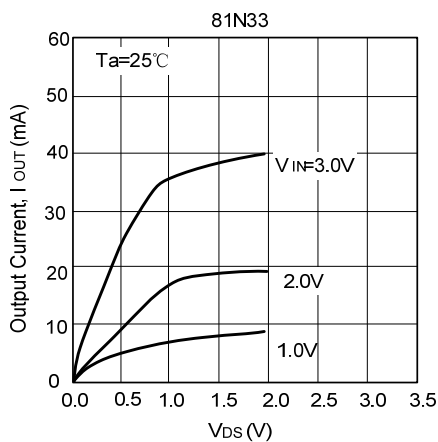
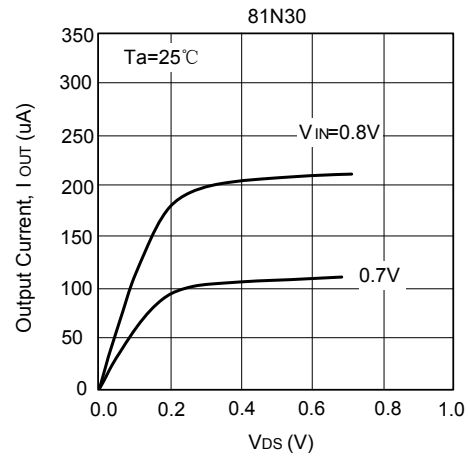
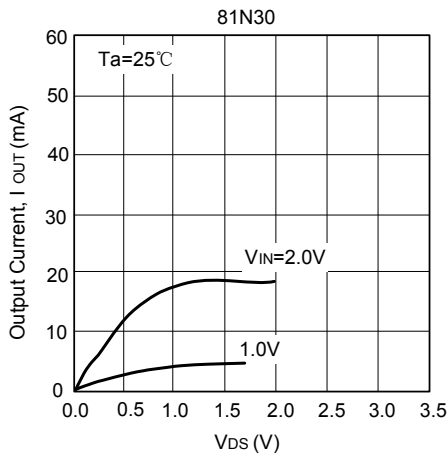
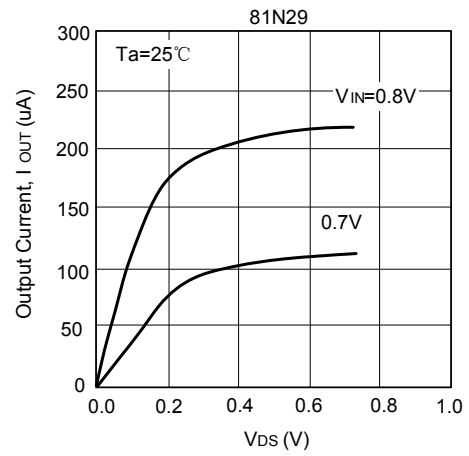
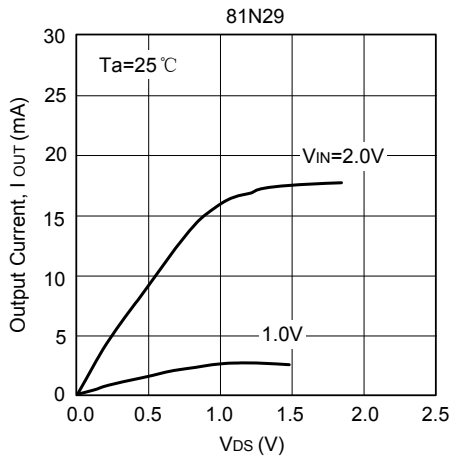
(5) N-CHANNEL DRIVE OUTPUT CURRENT vs. V_{DS}



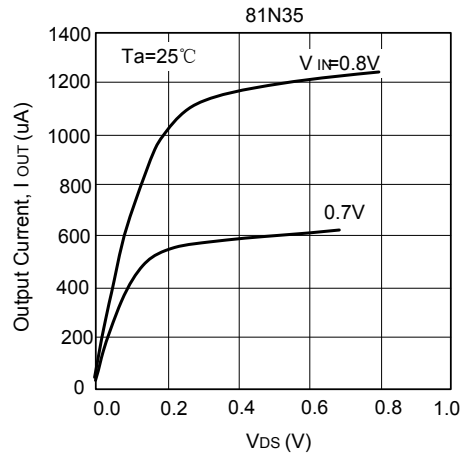
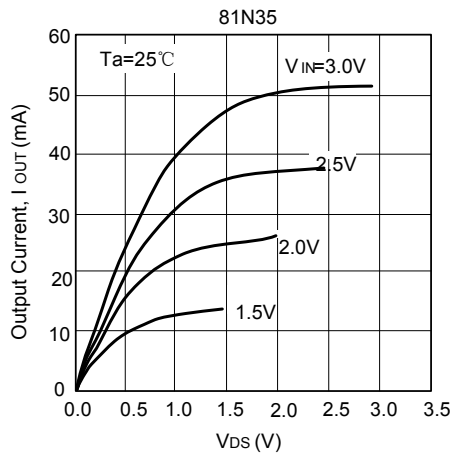
■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



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